

# **FEATURES**

- Rectangular Active Area
- Excellent Stability after EUV Exposure
- Windowless Package for Responsivity to 1 nm
- Ceramic Package

# **Electro-Optical Characteristics at 25 °C**

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	22.05 mm x 15.85 mm		331		mm²
Responsivity	See attached graph				A/W
Shunt Resistance	@ ± 10 mV	5			MOhms
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 μA	20	25		Volts
Capacitance, C	V <sub>R</sub> = 0 V			40	nF
Response Time, tr	RL = 50 Ω, V <sub>R</sub> = 0 V			10	usec

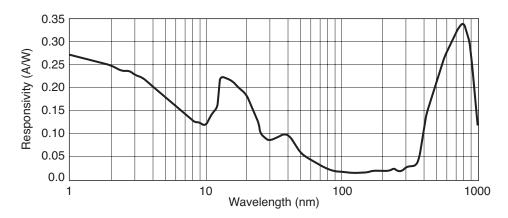
# **Thermal Parameters**

Storage and Operating Temperature Range					
Ambient	-10 ° to 40 °C				
Nitrogen or Vacuum	-20 ° to 80 °C				
Maximum Junction Temperature	70 °C				
Lead Soldering Temperature <sup>1</sup>	N/A				

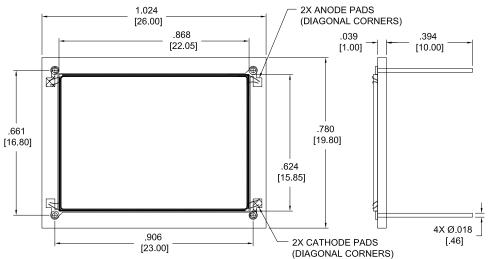
<sup>&</sup>lt;sup>1</sup> Soldering not recommended. Use with AXUV300CTS socket or equivalent.

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#### **Typical Photon Responsivity**



# **Package Information**



Dimensions are in inch [metric] units.

# **Ordering Information**

ODD-SXU-044 Large EUV High Speed Photodetector in a Ceramic Package

Specifications are subject to change without prior notice.

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